

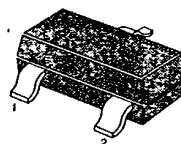
KSA812**PNP EPITAXIAL SILICON TRANSISTOR****LOW FREQUENCY AMPLIFIER**

- Complement to KSC1623
- Collector-Base Voltage $V_{CB0} = -60V$

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-60	V
Collector-Emitter Voltage	V_{CE0}	-50	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-100	mA
Collector Dissipation	P_C	150	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 ~ 150	$^\circ C$

SOT-23



1. Base 2. Emitter 3. Collector

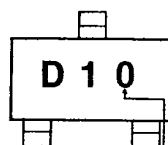
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = -60V, I_E = 0$			-0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = -6V, I_C = -1mA$	90	200	600	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$		-0.18	-0.3	V
Base-Emitter On Voltage	$V_{BE(on)}$	$I_C = -1mA, V_{CE} = -6V$	-0.55	-0.62	-0.65	V
Current Gain-Bandwidth Product	f_T	$I_C = -10mA, V_{CE} = -6V$		180		MHz
Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0$ $f = 1MHz$		4.5		pF

 h_{FE} CLASSIFICATION

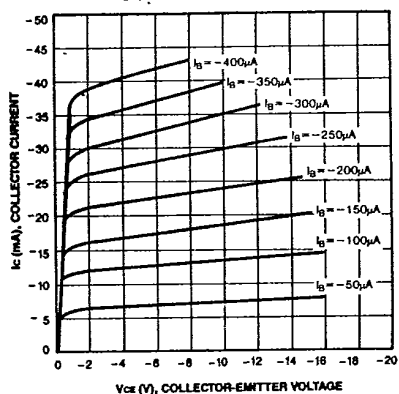
Classification	O	Y	G	L
h_{FE}	90-180	135-270	200-400	300-600

Marking

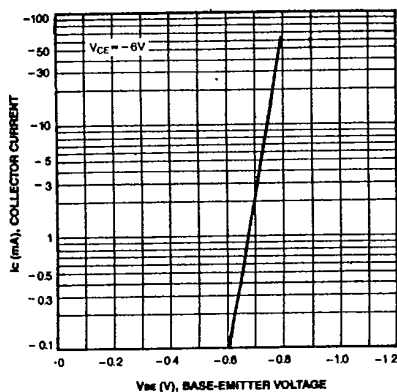
 h_{FE} grade

T-29-15

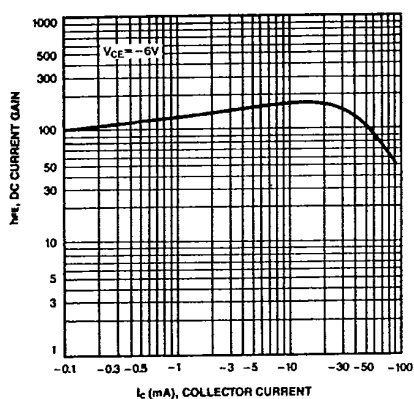
STATIC CHARACTERISTIC



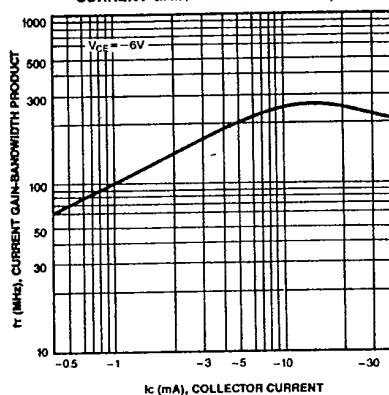
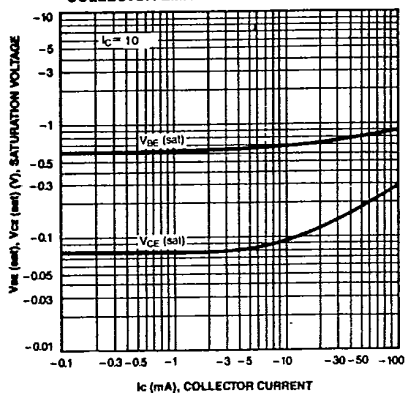
BASE-EMITTER ON VOLTAGE



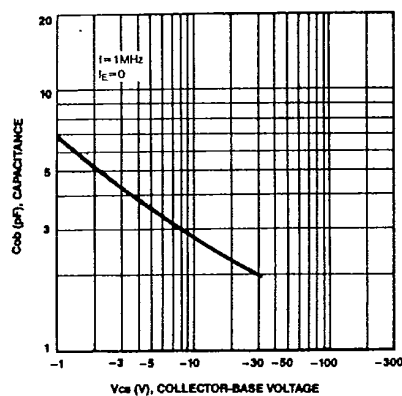
DC CURRENT GAIN



CURRENT GAIN-BANDWIDTH PRODUCT

BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE

COLLECTOR OUTPUT CAPACITANCE



3

